

Title (en)

SUBSTRATE FOR STRESSED SYSTEMS AND METHOD FOR CRYSTAL GROWTH ON SUCH A SUBSTRATE

Title (de)

SUBSTRAT FÜR VERSPANNTE SYSTEME UND VERFAHREN DES KRISTALLWACHSTUMS AUF EINEM SOLCHEN SUBSTRAT

Title (fr)

SUBSTRAT POUR SYSTEMES CONTRAINTS ET PROCEDE DE CROISSANCE CRISTALLINE SUR UN TEL SUBSTRAT

Publication

EP 1629526 A1 20060301 (FR)

Application

EP 04767192 A 20040527

Priority

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Abstract (en)

[origin: US2004241902A1] A stress absorbing microstructure assembly including a support substrate having an accommodation layer that has plurality of motifs engraved or etched in a surface, a buffer layer and a nucleation layer. The stress absorbing microstructure assembly may also include an insulating layer between the buffer layer and the nucleation layer. This assembly can receive thick epitaxial layers thereon with concern of causing cracking of such layers.

IPC 1-7

H01L 21/20; **H01L 21/762**

IPC 8 full level

B81C 1/00 (2006.01); **H01L 21/20** (2006.01); **H01L 21/762** (2006.01)

CPC (source: EP KR US)

B81C 1/00365 (2013.01 - EP US); **C30B 25/183** (2013.01 - EP US); **H01L 21/0237** (2013.01 - EP US); **H01L 21/0243** (2013.01 - EP US); **H01L 21/02439** (2013.01 - EP US); **H01L 21/0245** (2013.01 - EP US); **H01L 21/02513** (2013.01 - EP US); **H01L 21/02658** (2013.01 - EP US); **H01L 21/02664** (2013.01 - EP US); **H01L 21/187** (2013.01 - EP US); **H01L 21/20** (2013.01 - KR); **H01L 21/76254** (2013.01 - EP US); **B81C 2201/0191** (2013.01 - EP US)

Citation (search report)

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